

## Power MOSFET

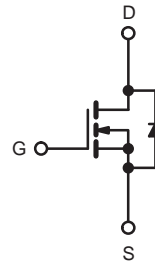
PRODUCT SUMMARY		
V <sub>DS</sub> (V)	100	
R <sub>DS(on)</sub> (Ω)	V <sub>GS</sub> = 10 V	0.020
Q <sub>g</sub> (Max.) (nC)	70	
Q <sub>gs</sub> (nC)	13	
Q <sub>gd</sub> (nC)	39	
Configuration	Single	

### FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Surface Mount
- Low-Profile Through-Hole
- Available in Tape and Reel
- Dynamic dV/dt Rating
- 150 °C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Compliant to RoHS Directive 2002/95/EC



**RoHS\***  
COMPLIANT  
HALOGEN  
**FREE**  
Available



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V <sub>DS</sub>	100	V
Gate-Source Voltage			V <sub>GS</sub>	±20	
Continuous Drain Current	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 25 °C	I <sub>D</sub>	70	A
		T <sub>C</sub> = 100 °C		56	
Pulsed Drain Current <sup>a, e</sup>			I <sub>DM</sub>	250	
Linear Derating Factor				1.0	W/°C
Single Pulse Avalanche Energy <sup>b, e</sup>			E <sub>AS</sub>	580	mJ
Avalanche Current <sup>a</sup>			I <sub>AR</sub>	20	A
Repetitive Avalanche Energy <sup>a</sup>			E <sub>AR</sub>	13	mJ
Maximum Power Dissipation	T <sub>C</sub> = 25 °C		P <sub>D</sub>	3.1	W
	T <sub>A</sub> = 25 °C			130	
Peak Diode Recovery dV/dt <sup>c, e</sup>			dV/dt	5.0	V/ns
Operating Junction and Storage Temperature Range			T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s			300 <sup>d</sup>	

### Notes


- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- V<sub>DD</sub> = 50 V, starting T<sub>J</sub> = 25 °C, L = 2.7 mH, R<sub>g</sub> = 25 Ω, I<sub>AS</sub> = 18 A (see fig. 12).
- I<sub>SD</sub> ≤ 20 A, di/dt ≤ 150 A/μs, V<sub>DD</sub> ≤ V<sub>DS</sub>, T<sub>J</sub> ≤ 150 °C.
- 1.6 mm from case.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

<b>THERMAL RESISTANCE RATINGS</b>				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient (PCB Mounted, Steady-State) <sup>a</sup>	R <sub>thJA</sub>	-	40	°C/W
Maximum Junction-to-Case (Drain)	R <sub>thJC</sub>	-	1.0	

**Note**

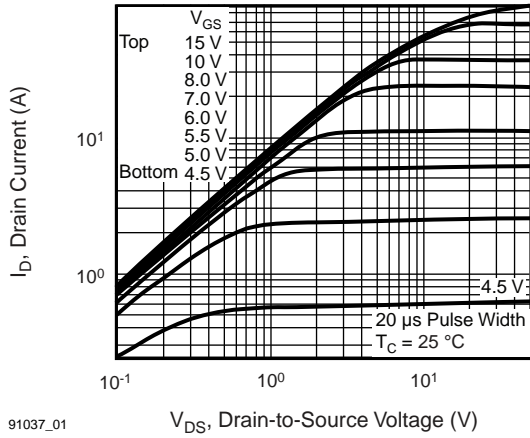
a. When mounted on 1" square PCB (FR-4 or G-10 material).

<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA		100	-	-	V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	Reference to 25 °C, I <sub>D</sub> = 1 mA <sup>c</sup>		-	0.29	-	V/°C
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		2.0	-	4.0	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V		-	-	25	μA
		V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C		-	-	250	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 11 A <sup>b</sup>	-	0.020	-	Ω
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 11 A <sup>d</sup>		6.7	-	-	S
<b>Dynamic</b>							
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1.0 MHz, see fig. 5 <sup>d</sup>		-	1300	-	pF
Output Capacitance	C <sub>oss</sub>			-	430	-	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	130	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, V <sub>DS</sub> = 160 V, see fig. 6 and 13 <sup>b, c</sup>	-	-	70	nC
Gate-Source Charge	Q <sub>gs</sub>			-	-	13	
Gate-Drain Charge	Q <sub>gd</sub>			-	-	39	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 50 V, I <sub>D</sub> = 20 A, R <sub>g</sub> = 9.1 Ω, R <sub>D</sub> = 5.4 Ω, see fig. 10 <sup>b, c</sup>		-	14	-	ns
Rise Time	t <sub>r</sub>			-	51	-	
Turn-Off Delay Time	t <sub>d(off)</sub>			-	45	-	
Fall Time	t <sub>f</sub>			-	36	-	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	20	A
Pulsed Diode Forward Current <sup>a</sup>	I <sub>SM</sub>			-	-	72	
Body Diode Voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 20 A, V <sub>GS</sub> = 0 V <sup>b</sup>		-	-	2.0	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>F</sub> = 20 A, di/dt = 100 A/μs <sup>b, c</sup>		-	300	610	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			-	3.4	7.1	μC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> and L <sub>D</sub> )					

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width ≤ 300 μs; duty cycle ≤ 2 %.
- c. Uses IRF640/SiHF640 data and test conditions.

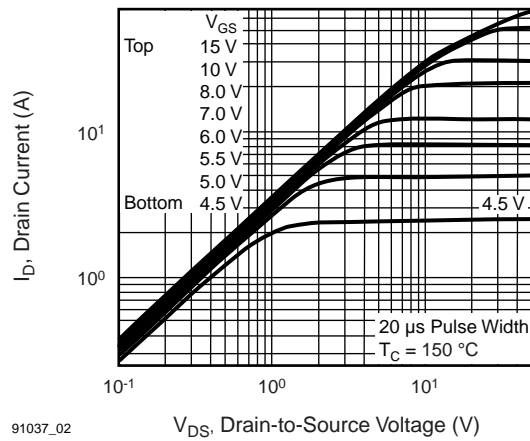
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



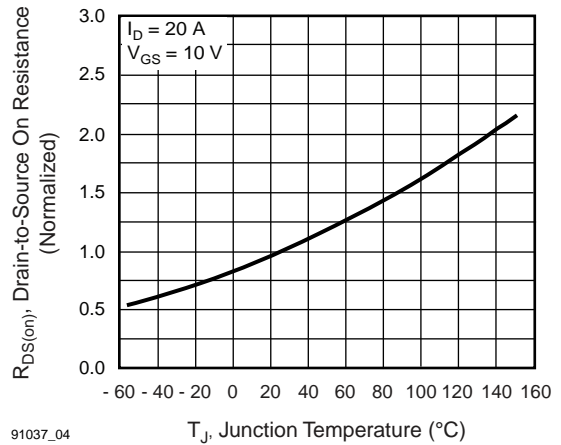
**Fig. 1 - Typical Output Characteristics,  $T_J = 25\text{ }^\circ\text{C}$**



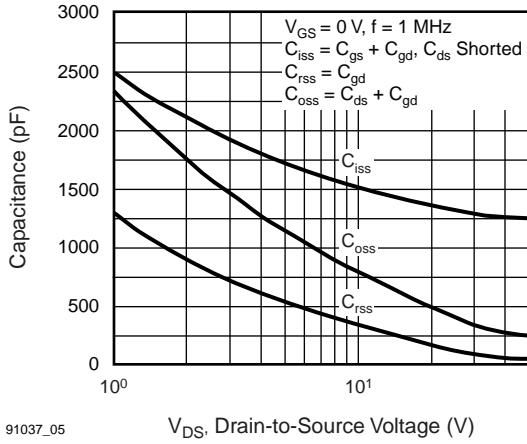
**Fig. 3 - Typical Transfer Characteristics**



**Fig. 2 - Typical Output Characteristics,  $T_J = 175\text{ }^\circ\text{C}$**



**Fig. 4 - Normalized On-Resistance vs. Temperature**



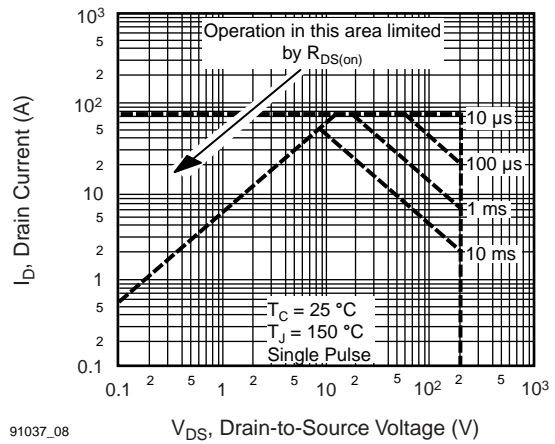
**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



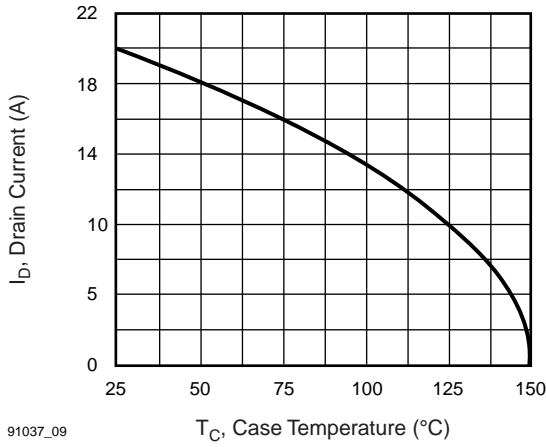
**Fig. 7 - Typical Source-Drain Diode Forward Voltage**



**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**



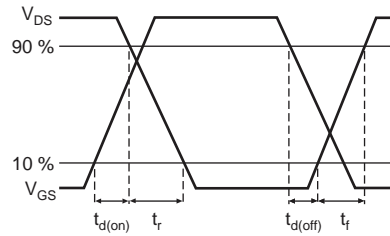
**Fig. 8 - Maximum Safe Operating Area**



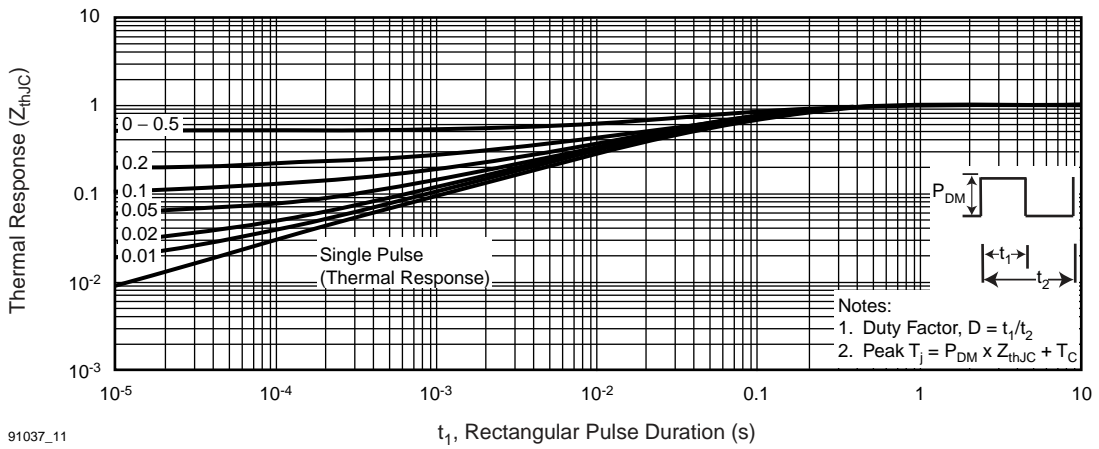
**Fig. 9 - Maximum Drain Current vs. Case Temperature**



**Fig. 10a - Switching Time Test Circuit**



**Fig. 10b - Switching Time Waveforms**



**Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**



Fig. 12a - Unclamped Inductive Test Circuit



Fig. 12b - Unclamped Inductive Waveforms

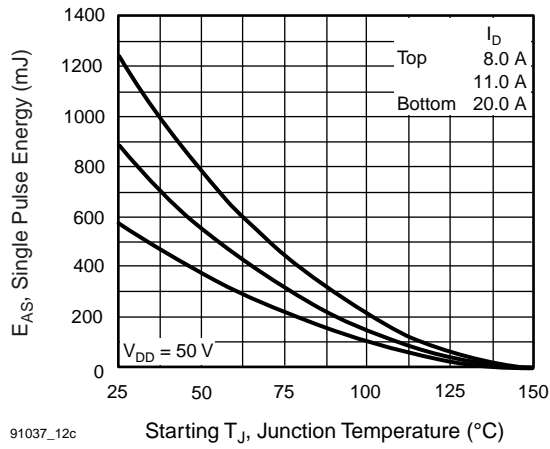


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

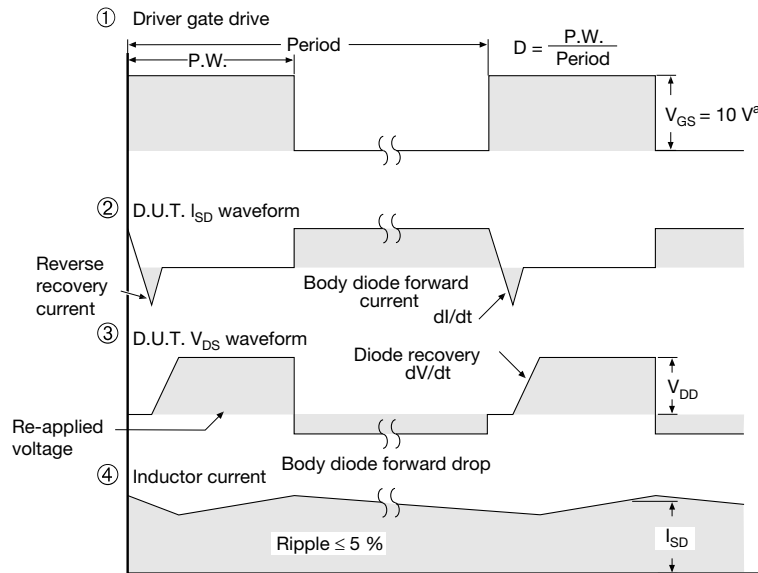
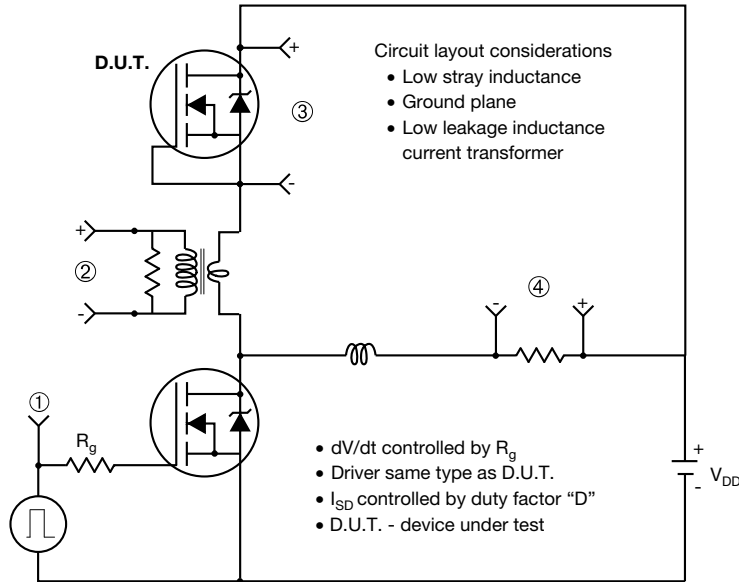


Fig. 13a - Basic Gate Charge Waveform



Fig. 13b - Gate Charge Test Circuit

**Peak Diode Recovery dV/dt Test Circuit**

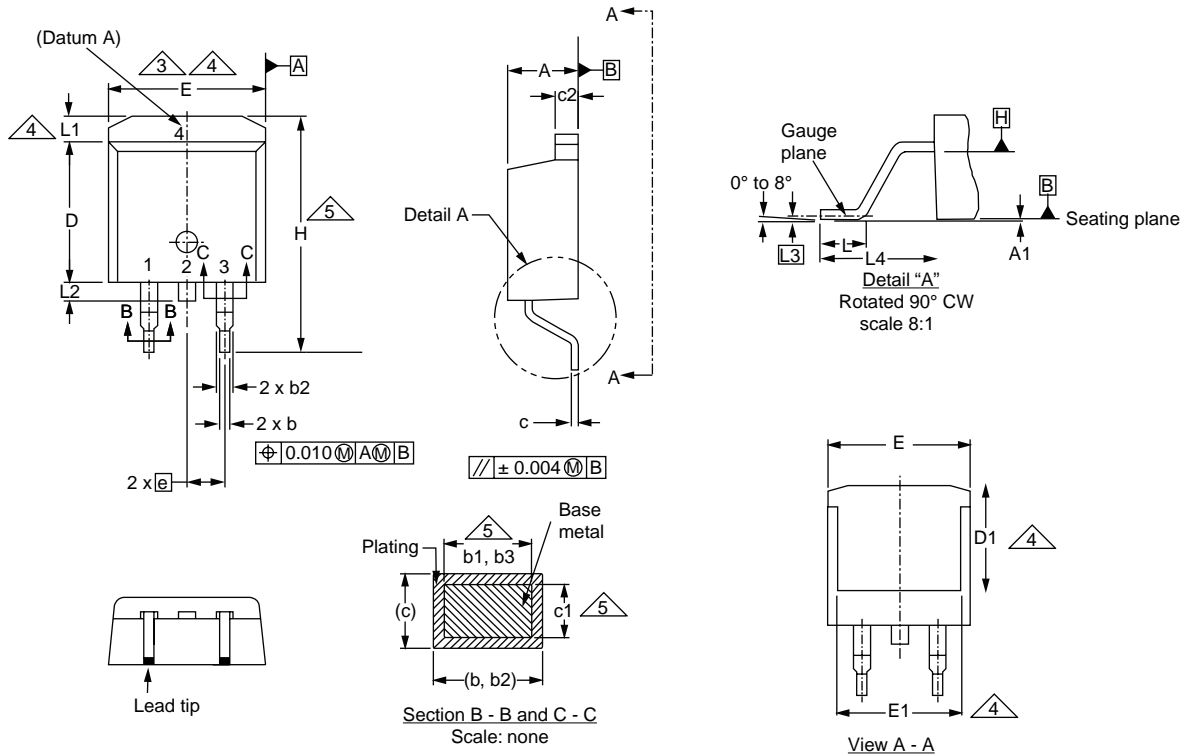


**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 14 - For N-Channel**

**TO-263AB (HIGH VOLTAGE)**



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

ECN: S-82110-Rev. A, 15-Sep-08  
DWG: 5970

**Notes**

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.



**RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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